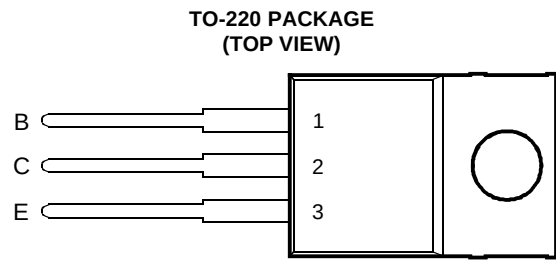


BD743, BD743A, BD743B, BD743C NPN SILICON POWER TRANSISTORS

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AUGUST 1978 - REVISED MARCH 1997

- Designed for Complementary Use with the BD744 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- 20 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD743	V_{CBO}	50	V
	BD743A		70	
	BD743B		90	
	BD743C		110	
Collector-emitter voltage ($I_B = 0$)	BD743	V_{CEO}	45	V
	BD743A		60	
	BD743B		80	
	BD743C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	15	A
Peak collector current (see Note 1)		I_{CM}	20	A
Continuous base current		I_B	5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	90	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating free air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



BD743, BD743A, BD743B, BD743C

NPN SILICON POWER TRANSISTORS

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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$	$I_B = 0$	(see Note 5)	BD743 45 BD743A 60 BD743B 80 BD743C 100			V
I_{CBO} Collector cut-off current	$V_{CE} = 50 \text{ V}$ $V_{CE} = 70 \text{ V}$ $V_{CE} = 90 \text{ V}$ $V_{CE} = 110 \text{ V}$ $V_{CE} = 50 \text{ V}$ $V_{CE} = 70 \text{ V}$ $V_{CE} = 90 \text{ V}$ $V_{CE} = 110 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	$T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$	BD743 BD743A BD743B BD743C BD743 BD743A BD743B BD743C		0.1 0.1 0.1 0.1 5 5 5 5	mA
I_{CEO} Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$		BD743/743A BD743B/743C		0.1 0.1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				0.5	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)	40 20 5		150	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 0.5 \text{ A}$ $I_B = 5 \text{ A}$	$I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)			1 3	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)			1 3	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ kHz}$	25			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ MHz}$	5			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.4	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]			MIN	TYP	MAX	UNIT
t_d Delay time	$I_C = 5 \text{ A}$ $V_{BE(off)} = -4.2 \text{ V}$	$I_{B(on)} = 0.5 \text{ A}$ $R_L = 6 \Omega$	$I_{B(off)} = -0.5 \text{ A}$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		20		ns
t_r Rise time					350		ns
t_s Storage time					500		ns
t_f Fall time					400		ns

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

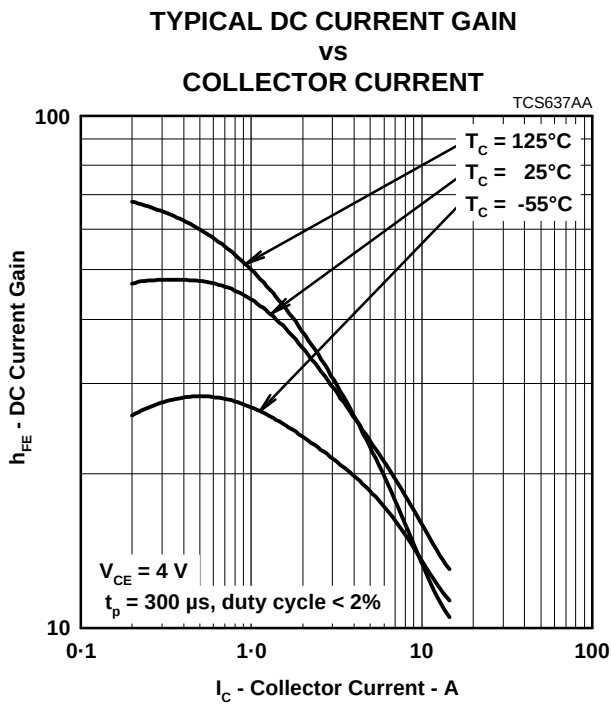


Figure 1.

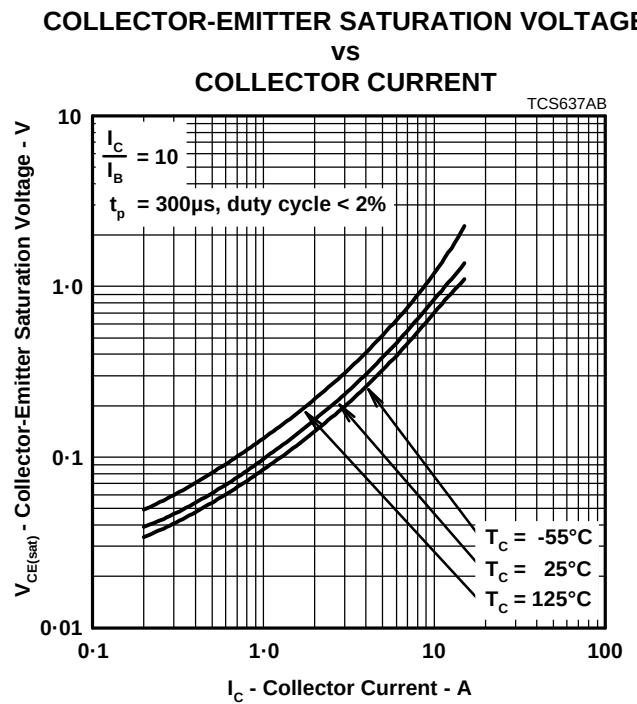


Figure 2.

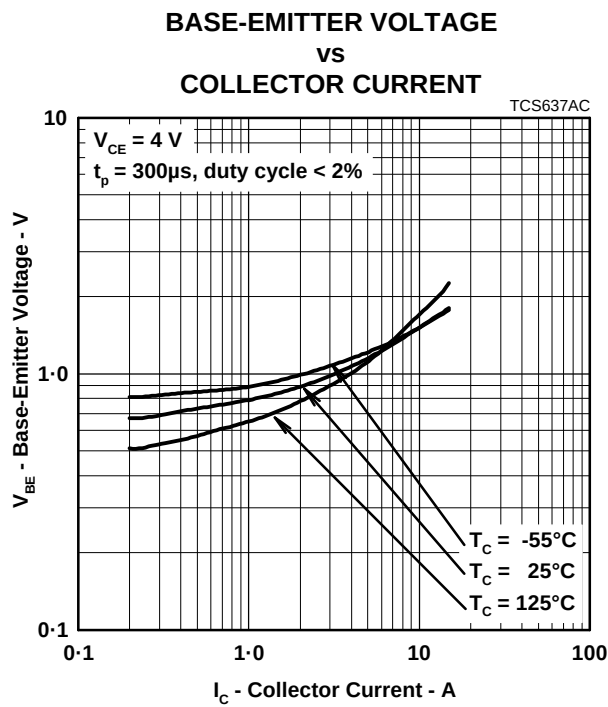


Figure 3.

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Figure 1 is a graph showing the relationship between Collector Current (I_C) in Amperes (A) on the Y-axis and Collector-Emitter Voltage (V_{CE}) in Volts (V) on the X-axis. The Y-axis is logarithmic, ranging from 0.01 to 100. The X-axis is also logarithmic, ranging from 1.0 to 1000.

The graph displays four curves representing different operating conditions, labeled on the right side:

- $t_p = 1 \text{ ms}, d = 0.1 = 10\%$
- $t_p = 10 \text{ ms}, d = 0.1 = 10\%$
- $t_p = 50 \text{ ms}, d = 0.1 = 10\%$
- DC Operation

The curves show that the maximum collector current (I_C) decreases as the pulse width (t_p) increases and the duty cycle (d) is maintained at 10%. The DC Operation curve shows the highest current capability for a given voltage, while the pulsed curves show lower current capabilities, with the 1 ms pulse width curve showing the lowest current capability.

On the left side of the graph, the device types are listed with arrows pointing to their respective curves:

- BD743
- BD743A
- BD743B
- BD743C

The curves for BD743, BD743A, and BD743B are very close to each other, while the curve for BD743C is slightly lower, indicating a slightly lower current capability for that device type under the same conditions.

Figure 4.

The graph shows the relationship between Maximum Power Dissipation (P_{tot}) and Case Temperature (T_c) for the TIS637AA device. The y-axis represents P_{tot} in Watts (W), ranging from 0 to 100. The x-axis represents T_c in degrees Celsius ($^{\circ}C$), ranging from 0 to 150. The power dissipation is constant at 90 W for temperatures up to 25 $^{\circ}C$. Beyond 25 $^{\circ}C$, the power dissipation decreases linearly, reaching 0 W at 150 $^{\circ}C$.

T_c - Case Temperature - $^{\circ}C$	P_{tot} - Maximum Power Dissipation - W
0	90
25	90
50	72
75	54
100	36
125	18
150	0

Figure 5.

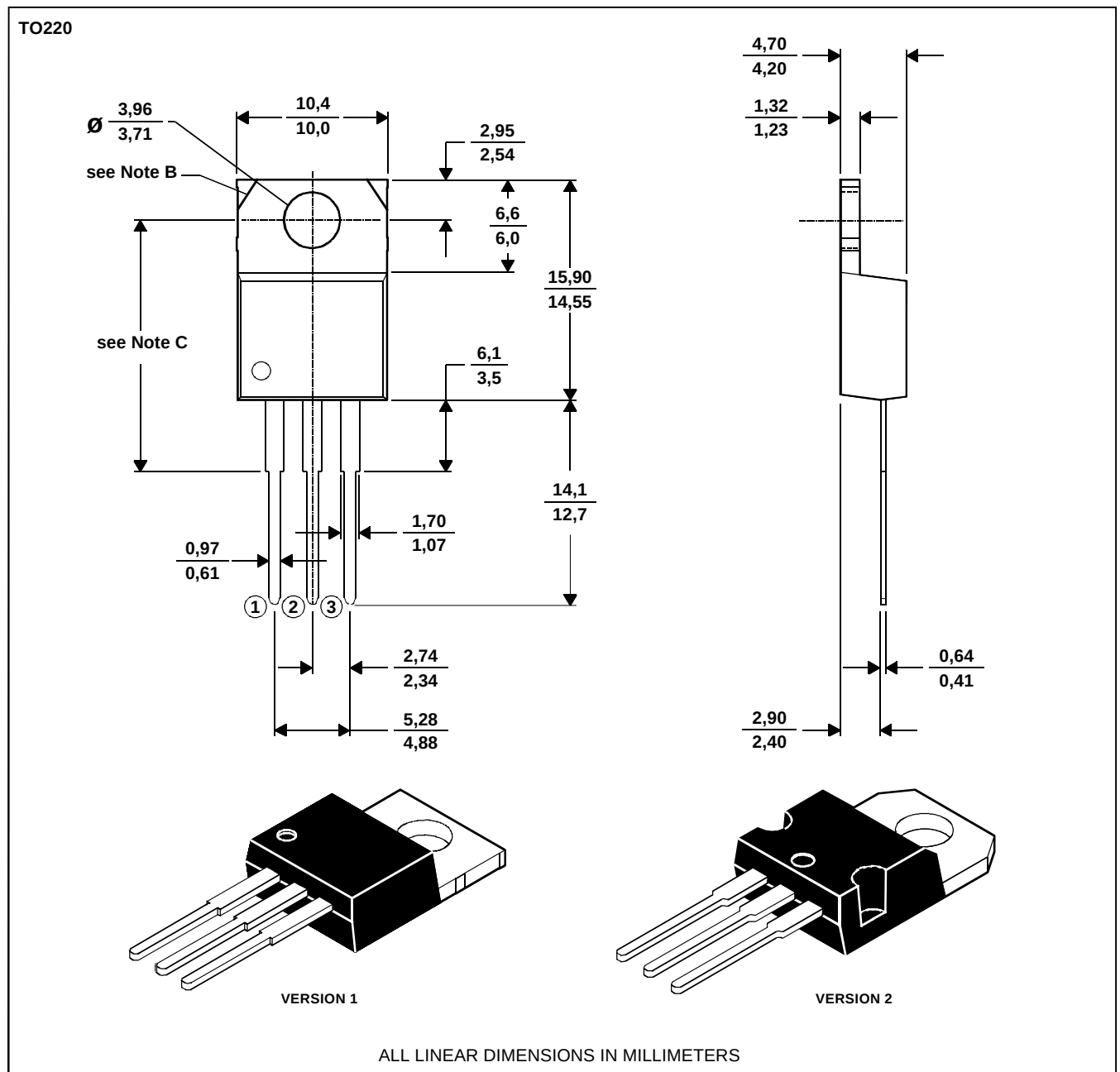
PRODUCT INFORMATION

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.

MDXXBE

BD743, BD743A, BD743B, BD743C

NPN SILICON POWER TRANSISTORS

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